Octal 3-State Inverting Buffer/Line Driver/Line Receiver

High-Performance Silicon-Gate CMOS

The MC74HC540A is identical in pinout to the LS540. The device inputs are compatible with Standard CMOS outputs. External pull-up resistors make them compatible with LSTTL outputs.

The HC540A is an octal inverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active-low output enables.

The HC540A is similar in function to the HC541A, which has noninverting outputs.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 124 FETs or 31 Equivalent Gates
- Pb-Free Packages are Available*



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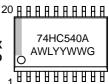
MARKING DIAGRAMS



PDIP-20 N SUFFIX CASE 738 20 AAAAAAAAAAA MC74HC540AN O AWLYYWWG

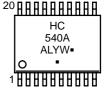


SOIC-20 DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E





SOEIAJ-20 F SUFFIX CASE 967

A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G = Pb-Free Package
Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

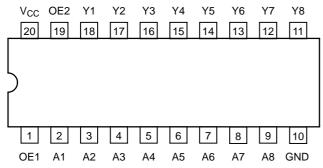


Figure 1. Pinout: 20-Lead Packages (Top View)

FUNCTION TABLE

| | Inputs | | Output V |
|-----|--------|---|----------|
| OE1 | OE2 | Α | Output Y |
| L | L | L | Н |
| L | L | Н | L |
| Н | Х | Х | Z |
| X | Н | Х | Z |

Z = High Impedance X = Don't Care

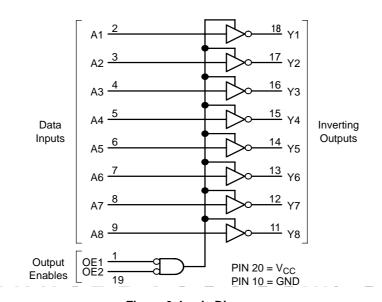


Figure 2. Logic Diagram

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-----------------|---------------------------|-----------------------|
| MC74HC540AN | PDIP-20 | 18 Units / Rail |
| MC74HC540ANG | PDIP-20 (Pb-Free) | 18 Units / Rail |
| MC74HC540ADW | SOIC-20 WIDE | 38 Units / Rail |
| MC74HC540ADWG | SOIC-20 WIDE (Pb-Free) | 38 Units / Rail |
| MC74HC540ADWR2 | SOIC-20 WIDE | 1000 Tape & Reel |
| MC74HC540ADWR2G | SOIC-20 WIDE (Pb-Free) | 1000 Tape & Reel |
| MC74HC540ADTR2 | TSSOP-20* | 2500 Tape & Reel |
| MC74HC540ADTR2G | TSSOP-20* | 2500 Tape & Reel |
| MC74HC540AF | SOEIAJ-20 | 40 Units / Rail |
| MC74HC540AFG | SOEIAJ-20 (Pb-Free) | 40 Units / Rail |
| MC74HC540AFEL | SOEIAJ-20 | 2000 Tape & Reel |
| MC74HC540AFELG | SOEIAJ-20 (Pb-Free) | 2000 Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

MAXIMUM RATINGS

| Symbol | F | Parameter | Value | Unit |
|----------------------|--|--|-----------------------------------|------|
| V _{CC} | DC Supply Voltage | | -0.5 to +7.0 | V |
| VI | DC Input Voltage | | -0.5 to $V_{CC} + 0.5$ | V |
| Vo | DC Output Voltage (Note 1) | | $-0.5 \le V_{O} \le V_{CC} + 0.5$ | V |
| I _{IK} | DC Input Diode Current | | ±20 | mA |
| I _{OK} | DC Output Diode Current | | ±35 | mA |
| Io | DC Output Sink Current | | ±35 | mA |
| I _{CC} | DC Supply Current per Supply Pin | | ±75 | mA |
| I _{GND} | DC Ground Current per Ground Pin | | ±75 | mA |
| T _{STG} | Storage Temperature Range | | -65 to +150 | °C |
| T_L | Lead Temperature, 1 mm from Case | or 10 Seconds | 260 | °C |
| TJ | Junction Temperature Under Bias | | + 150 | °C |
| θ_{JA} | Thermal Resistance | PDIP SOIC TSSOP | 67 96 128 | °C/W |
| P _D | Power Dissipation in Still Air at 85°C | PDIP SOIC TSSOP | 750 500 450 | mW |
| MSL | Moisture Sensitivity | | Level 1 | |
| F _R | Flammability Rating | Oxygen Index: 30% – 35% | UL 94 V0 @ 0.125 in | |
| V _{ESD} | ESD Withstand Voltage | Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4) | > 2000 > 200 > 1000 | ٧ |
| I _{LATCHUP} | Latchup Performance | Above V _{CC} and Below GND at 85°C (Note 5) | ±300 | mA |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. I_O absolute maximum rating must be observed.

- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit | |
|------------------------------------|--|--|-------------|--------------------|----|
| V _{CC} | DC Supply Voltage | (Referenced to GND) | 2.0 | 6.0 | V |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage | (Referenced to GND) | 0 | V _{CC} | V |
| T _A | Operating Temperature, All Package Types | | - 55 | + 125 | °C |
| t _r , t _f | Input Rise and Fall Time (Figure 3) | $V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$ | 0 0 0 | 1000 500 400 | ns |

6. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

DC CHARACTERISTICS (Voltages Referenced to GND)

| | | Guarantee | | aranteed Li | imit | | |
|-----------------|---|--|--------------------------|------------------------------|------------------------------|------------------------------|------|
| Symbol | Parameter | Condition | V _{CC} | –55 to 25°C | ≤ 85°C | ≤125°C | Unit |
| V _{IH} | Minimum High-Level Input Voltage | $V_{out} = 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 3.0 4.5 6.0 | 1.50 2.10 3.15 4.20 | 1.50 2.10 3.15 4.20 | 1.50 2.10 3.15 4.20 | V |
| V _{IL} | Maximum Low–Level Input Voltage | $\begin{aligned} V_{out} &= V_{CC} - 0.1 \text{ V} \\ I_{out} &\leq 20 \mu\text{A} \end{aligned}$ | 2.0 3.0 4.5 6.0 | 0.50 0.90 1.35 1.80 | 0.50 0.90 1.35 1.80 | 0.50 0.90 1.35 1.80 | V |
| V _{OH} | Minimum High-Level Output Voltage | $V_{in} = V_{IL}$ $ I_{out} \le 20 \mu A$ | 2.0 4.5 6.0 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | V |
| | | $\begin{split} V_{in} = V_{IL} & I_{out} \leq 3.6 \text{ mA} \\ I_{out} \leq 6.0 \text{ mA} \\ I_{out} \leq 7.8 \text{ mA} \end{split}$ | 3.0 4.5 6.0 | 2.48 3.98 5.48 | 2.34 3.84 5.34 | 2.20 3.70 5.20 | |
| V _{OL} | Maximum Low–Level Output Voltage | $V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$ | 2.0 4.5 6.0 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | V |
| | | $\begin{split} V_{in} = V_{IH} & I_{out} \leq 3.6 \text{ mA} \\ I_{out} \leq 6.0 \text{ mA} \\ I_{out} \leq 7.8 \text{ mA} \end{split}$ | 3.0 4.5 6.0 | 0.26 0.26 0.26 | 0.33 0.33 0.33 | 0.40 0.40 0.40 | |
| l _{in} | Maximum Input Leakage Current | V _{in} = V _{CC} or GND | 6.0 | ±0.1 | ±1.0 | ±1.0 | μΑ |
| I _{OZ} | Maximum Three–State Leakage Current | Output in High Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND | 6.0 | ±0.5 | ±5.0 | ±10.0 | μΑ |
| Icc | Maximum Quiescent Supply Current (per Package) | $V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$ | 6.0 | 4 | 40 | 160 | μΑ |

^{7.} Information on typical parametric values can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

| | | | Gu | Guaranteed Limit | | |
|--|--|--------------------------|-----------------------|-----------------------|-----------------------|------|
| Symbol | Parameter | V _{CC} | –55 to 25°C | ≤85°C | ≤125°C | Unit |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Input A to Output Y (Figures 3 and 5) | 2.0 3.0 4.5 6.0 | 80 30 18 15 | 100 40 23 20 | 120 55 28 25 | ns |
| t _{PLZ} , t _{PHZ} | Maximum Propagation Delay, Output Enable to Output Y (Figures 4 and 6) | 2.0 3.0 4.5 6.0 | 110 45 25 21 | 140 60 31 26 | 165 75 38 31 | ns |
| t _{PZL} , t _{PZH} | Maximum Propagation Delay, Output Enable to Output Y (Figures 4 and 6) | 2.0 3.0 4.5 6.0 | 110 45 25 21 | 140 60 31 26 | 165 75 38 31 | ns |
| t _{TLH} , t _{THL} | Maximum Output Transition Time, Any Output (Figures 3 and 5) | 2.0 3.0 4.5 6.0 | 60 22 12 10 | 75 28 15 13 | 90 34 18 15 | ns |
| C _{in} | Maximum Input Capacitance | | 10 | 10 | 10 | pF |
| C _{out} | Maximum 3-State Output Capacitance (Output in High Impedance State) | | 15 | 15 | 15 | pF |

^{8.} For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

| | | Typical @ 25°C, V _{CC} = 5.0 V, V _{EE} = 0 V | |
|----------|---|--|----|
| C_{PD} | Power Dissipation Capacitance (Per Buffer) (Note 9) | 35 | pF |

^{9.} Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

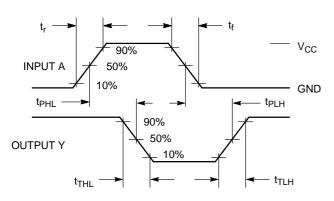


Figure 3. Switching Waveform

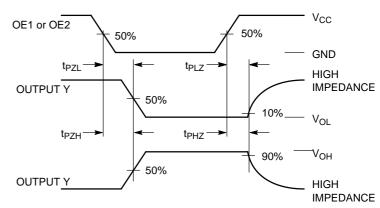
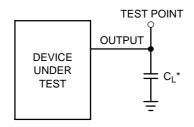
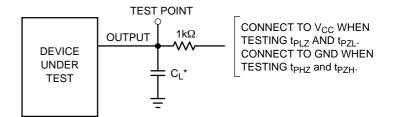


Figure 4. Switching Waveform



*Includes all probe and jig capacitance

Figure 5. Test Circuit



*Includes all probe and jig capacitance

Figure 6. Test Circuit

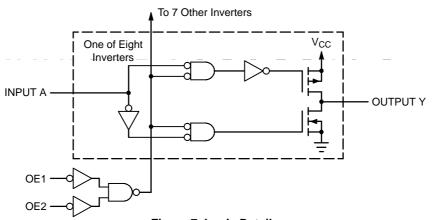


Figure 7. Logic Detail

PIN DESCRIPTIONS

INPUTS

A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8, 9)

Data input pins. Data on these pins appear in inverted form on the corresponding Y outputs, when the outputs are enabled.

CONTROLS

OE1, OE2 (PINS 1, 19)

Output enables (active—low). When a low voltage is applied to both of these pins, the outputs are enabled and the

device functions as an inverter. When a high voltage is applied to either input, the outputs assume the high impedance state.

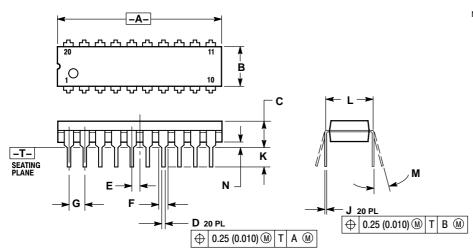
OUTPUTS

Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14, 13, 12, 11)

Device outputs. Depending upon the state of the output enable pins, these outputs are either inverting outputs or high–impedance outputs.

PACKAGE DIMENSIONS

PDIP-20 **N SUFFIX** PLASTIC DIP PACKAGE CASE 738-03 **ISSUE E**

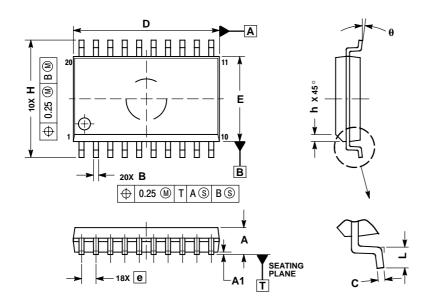


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.

| | INCHES | | MILLIN | ETERS |
|-----|--------|-----------|----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 1.010 | 1.070 | 25.66 | 27.17 |
| В | 0.240 | 0.260 | 6.10 | 6.60 |
| C | 0.150 | 0.180 | 3.81 | 4.57 |
| D | 0.015 | 0.022 | 0.39 | 0.55 |
| E | 0.050 | 0.050 BSC | | BSC |
| F | 0.050 | 0.070 | 1.27 | 1.77 |
| G | 0.100 | BSC | 2.54 BSC | |
| J | 0.008 | 0.015 | 0.21 | 0.38 |
| K | 0.110 | 0.140 | 2.80 | 3.55 |
| L | 0.300 | 0.300 BSC | | BSC |
| M | 0° | 15° | 0° | 15° |
| N | 0.020 | 0.040 | 0.51 | 1.01 |

SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G



NOTES:

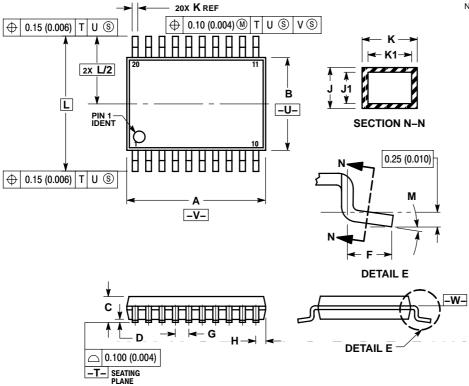
- NOTES:

 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIN | IETERS |
|-----|--------|--------|
| DIM | MIN | MAX |
| Α | 2.35 | 2.65 |
| A1 | 0.10 | 0.25 |
| В | 0.35 | 0.49 |
| С | 0.23 | 0.32 |
| D | 12.65 | 12.95 |
| E | 7.40 | 7.60 |
| е | 1.27 | BSC |
| Н | 10.05 | 10.55 |
| h | 0.25 | 0.75 |
| L | 0.50 | 0.90 |
| A | 0 ° | 7 ° |

PACKAGE DIMENSIONS

TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B**



NOTES:

- DTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SILLIAL NOT EXCEPT A 45 SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER
- SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

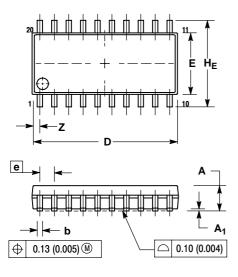
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

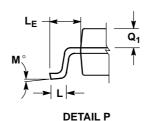
 6. TERMINAL NUMBERS ARE SHOWN.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

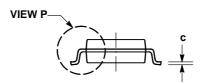
| | MILLIMETERS | | INC | HES |
|-----|-------------|------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 6.40 | 6.60 | 0.252 | 0.260 |
| В | 4.30 | 4.50 | 0.169 | 0.177 |
| С | | 1.20 | | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 | BSC | 0.026 | BSC |
| Н | 0.27 | 0.37 | 0.011 | 0.015 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | | 0.252 BSC | |
| M | 0° | 8° | 0° | 8° |

PACKAGE DIMENSIONS

SOEIAJ-20 **F SUFFIX** CASE 967-01 **ISSUE O**







- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
 - DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED
- AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

| | MILLIN | MILLIMETERS INC | | HES |
|----------------|----------|-----------------|-------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | | 2.05 | | 0.081 |
| A ₁ | 0.05 | 0.20 | 0.002 | 0.008 |
| b | 0.35 | 0.50 | 0.014 | 0.020 |
| C | 0.18 | 0.27 | 0.007 | 0.011 |
| D | 12.35 | 12.80 | 0.486 | 0.504 |
| Е | 5.10 | 5.45 | 0.201 | 0.215 |
| е | 1.27 BSC | | 0.050 | BSC |
| HE | 7.40 | 8.20 | 0.291 | 0.323 |
| L | 0.50 | 0.85 | 0.020 | 0.033 |
| LE | 1.10 | 1.50 | 0.043 | 0.059 |
| M | 0 ° | 10 ° | 0 ° | 10 ° |
| Q_1 | 0.70 | 0.90 | 0.028 | 0.035 |
| Z | | 0.81 | | 0.032 |

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